

BZT52BxxxS Series

200mW Surface Mount Zener Diodes -2.4V-43V

Features

- Silicon epitaxial planar chip structure.
- Wide zener reverse voltage range 2.0V to 43V.
- Small package size for high density applications.
- Ideally suited for automated assembly processes.
- Pb-free package is available
- We declare that the material of product compliance with RoHS requirements.
- Compliant to Halogen-free

Mechanical data

• Epoxy:UL94-V0 rated flame retardant

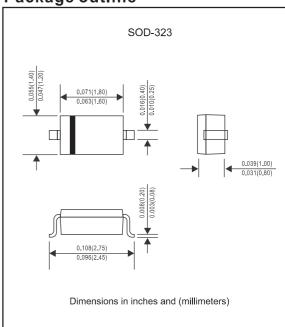
• Case: Molded plastic, SOD-323

 Terminals: Solder plated, solderable per MIL-STD-750, Method 2026

• Polarity: Indicated by cathode band

• Mounting Position : Any

Package outline



Maximum ratings (at T_A=25°C unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 10 mA	V _F			0.9	V
Power dissipation	T _A =25°C (note 1)	P _D			200	mW
Thermal resistance	Junction to ambient (note 1) Junction to case (note 1)	R _{eja} R _{ejc}		625 350		°C/W
Operating junction temperature range		T	-55		+150	°C
Storage temperature range		T _{STG}	-55		+150	°C

Note 1: Mounted on FR-4 minimum pad



BZT52BxxxS Series

200mW Surface Mount Zener Diodes -2.4V-43V

Electrical characteristics (at T_A=25°C unless otherwise noted)

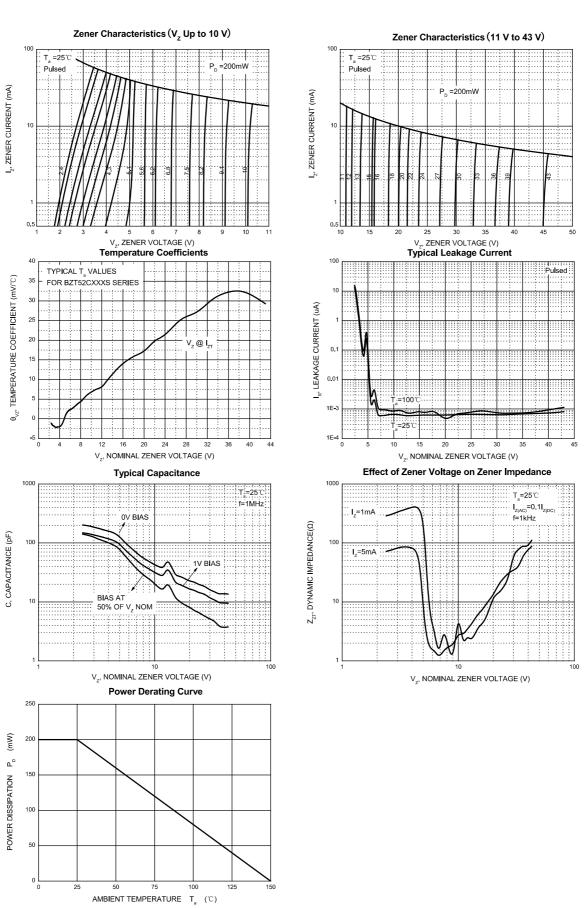
Type Number	e Type		Zener Voltage Range (Note 2)		Maximum Zener Impedance (Note 3)		Maximum Reverse Current		Typical Temperature Coefficent @Izтc		Test Current I _{ZTC}		
			V _z @l _{zT}		I _{ZT}	Z _{ZT} @I _{ZT}	Z _{zK} @ I _{zK}	I zk	I _R V _R		mV/°C		
		Nom(V)	Min(V)	Max(V)	mA	Ω		mA	μΑ	V	Min	Max	mA
BZT52B2V4S	2WX	2.4	2.35	2.45	5	100	600	1.0	50	1.0	-3.5	0	5
BZT52B2V7S	2W1	2.7	2.65	2.75	5	100	600	1.0	20	1.0	-3.5	0	5
BZT52B3V0S	2W2	3.0	2.94	3.06	5	95	600	1.0	10	1.0	-3.5	0	5
BZT52B3V3S	2W3	3.3	3.23	3.37	5	95	600	1.0	5	1.0	-3.5	0	5
BZT52B3V6S	2W4	3.6	3.53	3.67	5	90	600	1.0	5	1.0	-3.5	0	5
BZT52B3V9S	2W5	3.9	3.82	3.98	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52B4V3S	2W6	4.3	4.21	4.39	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52B4V7S	2W7	4.7	4.61	4.79	5	80	500	1.0	3	2.0	-3.5	0.2	5
BZT52B5V1S	2W8	5.1	5.00	5.20	5	60	480	1.0	2	2.0	-2.7	1.2	5
BZT52B5V6S	2W9	5.6	5.49	5.71	5	40	400	1.0	1	2.0	-2.0	2.5	5
BZT52B6V2S	2WA	6.2	6.08	6.32	5	10	150	1.0	3	4.0	0.4	3.7	5
BZT52B6V8S	2WB	6.8	6.66	6.94	5	15	80	1.0	2	4.0	1.2	4.5	5
BZT52B7V5S	2WC	7.5	7.35	7.65	5	15	80	1.0	1	5.0	2.5	5.3	5
BZT52B8V2S	2WD	8.2	8.04	8.36	5	15	80	1.0	0.7	5.0	3.2	6.2	5
BZT52B9V1S	2WE	9.1	8.92	9.28	5	15	100	1.0	0.5	6.0	3.8	7.0	5
BZT52B10S	2WF	10	9.80	10.20	5	20	150	1.0	0.2	7.0	4.5	8.0	5
BZT52B11S	2WG	11	10.78	11.22	5	20	150	1.0	0.1	8.0	5.4	9.0	5
BZT52B12S	2WH	12	11.76	12.24	5	25	150	1.0	0.1	8.0	6.0	10.0	5
BZT52B13S	2WI	13	12.74	13.26	5	30	170	1.0	0.1	8.0	7.0	11.0	5
BZT52B15S	2WJ	15	14.70	15.30	5	30	200	1.0	0.1	10.5	9.2	13.0	5
BZT52B16S	2WK	16	15.68	16.32	5	40	200	1.0	0.1	11.2	10.4	14.0	5
BZT52B18S	2WL	18	17.64	18.36	5	45	225	1.0	0.1	12.6	12.4	16.0	5
BZT52B20S	2WM	20	19.60	20.40	5	55	225	1.0	0.1	14.0	14.4	18.0	5
BZT52B22S	2WN	22	21.56	22.44	5	55	250	1.0	0.1	15.4	16.4	20.0	5
BZT52B24S	2WO	24	23.52	24.48	5	70	250	1.0	0.1	16.8	18.4	22.0	5
BZT52B27S	2WP	27	26.46	27.54	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52B30S	2WQ	30	29.40	30.60	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52B33S	2WR	33	32.34	33.66	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52B36S	2WS	36	35.28	36.72	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52B39S	2WT	39	38.22	39.78	2	130	350	0.5	0.1	27.3	33.4	41.2	2
BZT52B43S	2WU	43	42.14	43.86	2	130	350	0.5	0.1	29.4	36.4	45.2	2

Notes: 1. Device mounted on ceramic PCB:7.6mm x 9.4mm x 0.87mm with pad areas 25mm²

2. Short duration test pulse used to minimize self-heating effect

3 f = 1kHz

Rating and characteristic curves (BZT52BxxxS Series)





Document ID	Issued Date	Revised Date	Revision	Page.
AS-3100023	2003/03/08	2012/05/16	D	4

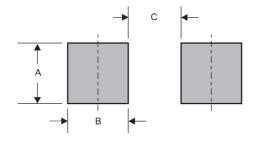
BZT52BxxxS Series

200mW Surface Mount Zener Diodes -2.4V-43V

Pinning information

Pin	Simplified outline	Symbol		
Pin1 cathode Pin2 anode	1 🗆 🗆 2	1 2		

Suggested solder pad layout



Dimensions in inches and (millimeters)

PACKAGE	А	В	С
SOD-323	0.033 (0.83)	0.025 (0.63)	0.063 (1.60)